

DESCRIPTION

The H11F series consists of a Gallium-Aluminum-Arsenide IRED emitting diode coupled to a symmetrical bilateral silicon photodetector. The detector is electrically isolated from the input and performs like an ideal isolated FET designed for distortion-free control of low level AC and DC analog signals. The H11F series devices are mounted in dual in-line packages.

FEATURES

As a remote variable resistor

- $\leq 100\Omega$ to $\geq 300~M\Omega$
- \geq 99.9% linearity
- \leq 15 pF shunt capacitance
- \geq 100 G Ω I/O isolation resistance

FAIRCHILD

SEMICONDUCTOR®

As an analog switch

- · Extremely low offset voltage
- 60 V_{pk-pk} signal capability
- No charge injection or latch-up
- t_{on}, t_{off} ≤ 15 µS
- UL recognized (File #E90700)
- VDE recognized (File #E94766)
- Ordering option '300' (e.g. H11F1.300)

APPLICATIONS

As a variable resistor -

- · Isolated variable attenuator
- Automatic gain control
- · Active filter fine tuning/band switching

As an analog switch -

- Isolated sample and hold circuit
- Multiplexed, optically isolated A/D conversion

Absolute Maximum Ratings (T _A = 25°C unless otherwise specified)						
Parameter	Symbol	Device	Value	Units		
TOTAL DEVICE						
Storage Temperature	T _{STG}	All	-55 to +150	°C		
Operating Temperature	T _{OPR}	All	-55 to +100	°C		
Lead Solder Temperature	T _{SOL}	All	260 for 10 sec	°C		
EMITTER						
Continuous Forward Current	١ _F	All	60	mA		
Reverse Voltage	V _R	All	5	V		
Forward Current - Peak (10 µs pulse, 1% duty cycle)	I _{F(pk)}	All	1	А		
LED Power Dissipation 25°C Ambient	Р	All	100	mW		
Derate Linearly From 25°C	PD	All	1.33	mW/°C		
DETECTOR						
Detector Power Dissipation @ 25°C	Р	All	300	mW		
Derate linearly from 25°C	PD	All	4.0	mW/°C		
Proakdown Valtage (either palarity)	D\/	H11F1, H11F2	±30	V		
Breakdown Voltage (either polarity)	BV ₄₋₆	H11F3	±15	V		
Continuous Detector Current (either polarity)	I ₄₋₆	All	±100	mA		

ELECTRICAL CHARACTERISTICS (T_A = 25°C Unless otherwise specified.)

INDIVIDUAL COMPONENT CHARACTERISTICS							
Parameter	Test Conditions	Symbol	Device	Min	Тур*	Мах	Unit
EMITTER							
Input Forward Voltage	l _F = 16 mA	V _F	All		1.3	1.75	V
Reverse Leakage Current	V _R = 5 V	I _R	All			10	μA
Capacitance	V = 0 V, f = 1.0 MHz	CJ	All		50		pF
OUTPUT DETECTOR							
Breakdown Voltage		BV ₄₋₆	H11F1, H11F2	30			v
Either Polarity	$I_{4-6} = 10\mu A, I_F = 0$	DV ₄₋₆	H11F3	15]
Off-State Dark Current	V ₄₋₆ = 15 V, I _F = 0	1	All			50	nA
OII-State Dark Current	$V_{4-6} = 15 \text{ V}, \text{ I}_{\text{F}} = 0, \text{ T}_{\text{A}} = 100^{\circ}\text{C}$	I ₄₋₆	All			50	μA
Off-State Resistance	V ₄₋₆ = 15 V, I _F = 0	R ₄₋₆	All	300			MΩ
Capacitance	$V_{4-6} = 15 \text{ V}, \text{ I}_{\text{F}} = 0, \text{ f} = 1\text{MHz}$	C ₄₋₆	All			15	pF

FAIRCHILD

ISOLATION CHARACTERISTICS						
Parameter	Test Conditions	Symbol	Min	Тур*	Max	Units
Input-Output Isolation Voltage	f = 60Hz, t = 1 min.	V _{ISO}	5300			Vac (rms)
Isolation Resistance	V _{I-O} = 500 VDC	R _{ISO}	10 ¹¹			Ω
Isolation Capacitance	V _{I-O} = 0, f = 1.0 MHz	C _{ISO}			2	pF

TRANSFER CHARACTERISTICS ($T_A = 25^{\circ}C$ Unless otherwise specified.)							
DC Characteristics	Test Conditions	Symbol	Device	Min	Тур*	Мах	Units
			H11F1			200	
On-State Resistance	I _F = 16 mA, I ₄₋₆ = 100 μA	R ₄₋₆	H11F2			330	Ω
			H11F3			470	
			H11F1			200	
On-State Resistance	I _F = 16 mA, Ι ₆₋₄ = 100 μA	R ₆₋₄	H11F2			330	Ω
			H11F3			470	
Resistance, non-linearity and assymetry	$I_F = 16mA$, $I_{4-6} = 25 \ \mu A \ RMS$, f = 1kHz		All			0.1	%
AC Characteristics	Test Conditions	Symbol	Device	Min	Тур*	Max	Units
Turn-On Time	$R_L = 50\Omega, I_F = 16mA, V_{4-6} = 5V$	t _{on}	All			25	μS
Turn-Off Time	$R_L = 50\Omega, I_F = 16mA, V_{4-6} = 5V$	t _{off}	All			25	μS

FAIRCHILD

PHOTO FET OPTOCOUPLERS

H11F1 H11F2 H11F3

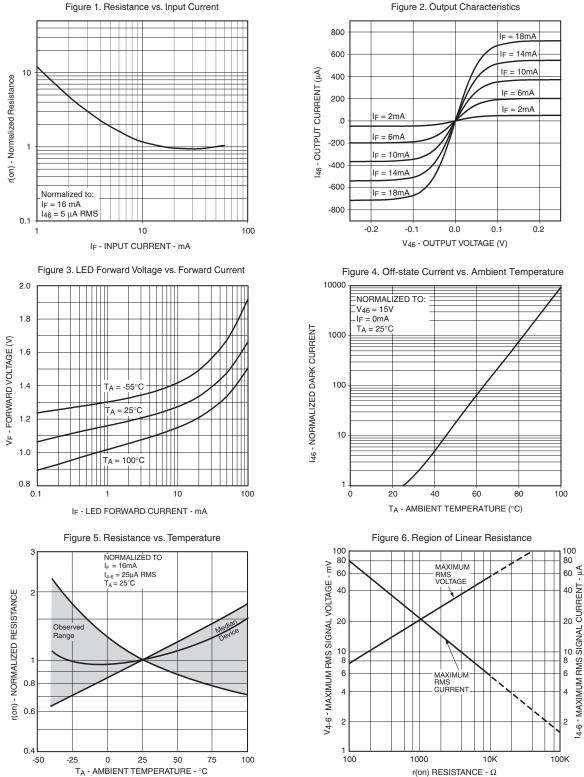


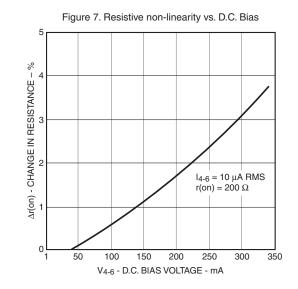
Figure 1. Resistance vs. Input Current

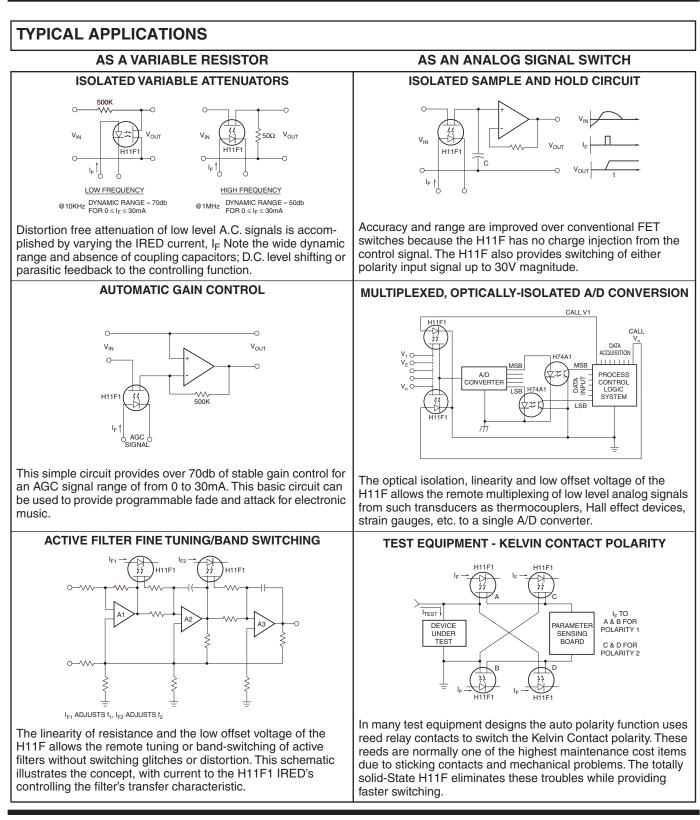
FAIRCHILD

PHOTO FET OPTOCOUPLERS

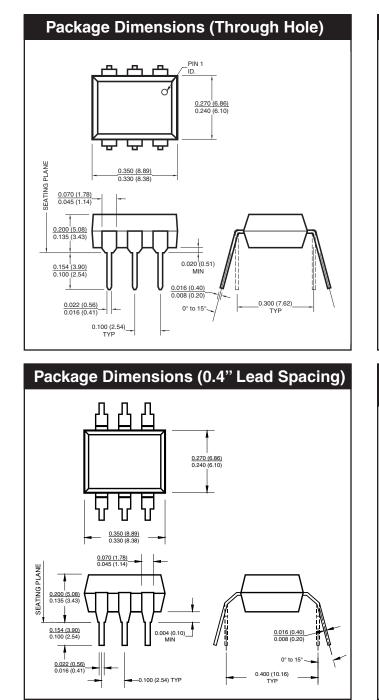


H11F1 H11F2 H11F3





FAIRCHILD

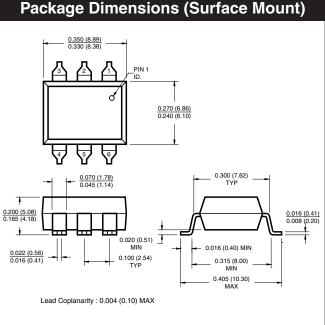


FAIRCHILD

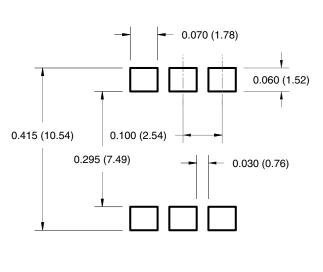
SEMICONDUCTOR®

NOTE

All dimensions are in inches (millimeters)



Recommended Pad Layout for Surface Mount Leadform



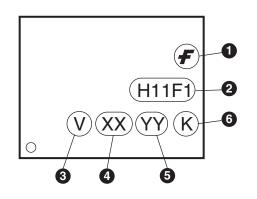
ORDERING INFORMATION

FAIRCHILD

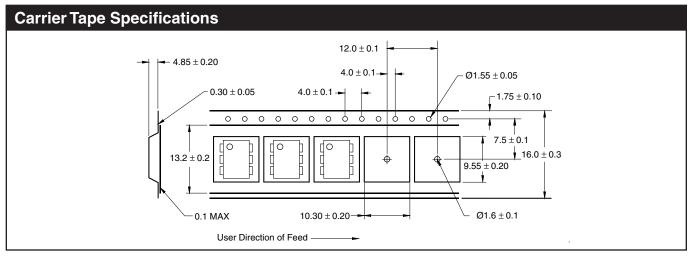
SEMICONDUCTOR®

Option	Order Entry Identifier	Description
S	.S	Surface Mount Lead Bend
SD	.SD	Surface Mount; Tape and Reel
W	.W.	0.4" Lead Spacing
300	.300	VDE 0884
300W	.300W	VDE 0884, 0.4" Lead Spacing
3S	.3S	VDE 0884, Surface Mount
3SD	.3SD	VDE 0884, Surface Mount, Tape and Reel

MARKING INFORMATION



Definitions					
1	Fairchild logo				
2	Device number				
3	VDE mark (Note: Only appears on parts ordered with VDE option – See order entry table)				
4	Two digit year code, e.g., '03'				
5	Two digit work week ranging from '01' to '53'				
6	Assembly package code				



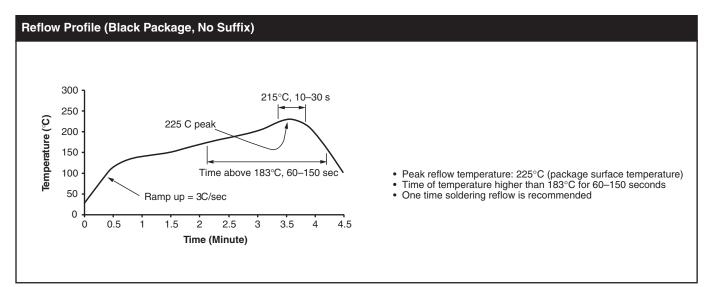
NOTE

All dimensions are in inches (millimeters)

FAIRCHILD

SEMICONDUCTOR®

Tape and reel quantity is 1,000 units per reel





SEMICONDUCTOR®

PHOTO FET OPTOCOUPLERS

H11F1 H11F2 H11F3

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF THE PRESIDENT OF FAIRCHILD SEMICONDUCTOR CORPORATION. As used herein:

- Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
- 2. A critical component in any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.



Home >> Find products >>

H11F3

6-Pin DIP Bilateral Analog FET Output Optocoupler

Contents

•<u>General description</u> •<u>Features</u> •<u>Applications</u> •Ordering information

General description

•Product status/pricing/packaging

Order Samples
Application notes
Safety agency certificates
Qualification Support



BUY

Related Links

Request samples

How to order products

Product Change Notices (PCNs)

<u>Support</u>

Sales support

Quality and reliability

Design center

The H11F series consists of a Gallium-Aluminum-Arsenide IRED emitting diode coupled to a symmetrical bilateral silicon photo-detector. The detector is electrically isolated from the input and performs like an ideal isolated FET designed for distortion-free control of low level AC and DC analog signals. The H11F series devices are mounted in dual in-line packages.

back to top

Features

As a remote variable resistor:

- ≤100 Ω to ≥ 300 MΩ
- ≥99.9% linearity
- ≤15 pF shunt capacitance
- ≥100 GΩ I/O isolation resistance

As an analog switch:

- Extremely low offset voltage
- 60 V_{pk-pk} signal capability

This page Print version

E- 1

e-mail this datasheet

- No charge injection or latchup
- t_{on}, t_{off} ≤15µs
- UL recognized (File #E90700)
- VDE recognized (File #E94766)
 - Ordering option '300' (e.g. H11F1.300)

back to top

Applications

As a variable resistor:

- Isolated variable attenuator
- Automatic gain control
- Active filter fine tuning/band switching

As an analog switch:

- Isolated sample and hold circuit
- Multiplexed, optically isolated A/D conversion

back to top

Ordering information

The following options can be ordered with this part:

Option	Order Entry Identifier	Description
S	.S	Surface Mount Lead Bend
SD	.SD	Surface Mount; Tape and Reel
W	.W	0.4" Lead Spacing
300	.300	VDE 0884
300W	.300W	VDE 0884; 0.4" Lead Spacing
3S	.3S	VDE 0884, Surface Mount
3SD	.3SD	VDE 0884, Surface Mount, Tape and Reel

back to top



Product	Product status	Pb-free Status	Package type	Leads	Packing method
H11F3	Lifetime Buy	Ø	DIP-B	6	BULK
H11F3300	Lifetime Buy	Ø	DIP-B	6	BULK
H11F3300W	Lifetime Buy	Ø	DIP-B	6	BULK
H11F33S	Lifetime Buy	Ø	SMDIP-B	6	BULK
H11F33SD	Lifetime Buy	Ø	SMDIP-B	6	TAPE REEL
H11F3S	Lifetime Buy	Ø	SMDIP-B	6	BULK
H11F3SD	Lifetime Buy	Ø	SMDIP-B	6	TAPE REEL
H11F3W	Lifetime Buy	Ø	DIP-B	6	BULK

Indicates product with Pb-free second-level interconnect. For more information click here.

back to top

Application notes

AN-7511: Insulated-Gate Transistors Simplify AC-Motor Speed Control (493 K) Jul 27, 2007

back to top

Safety agency certificates

Certificate		Agency
<u>E90700, Vol. 1</u> (936 K)	UL (1577)	Underwriters Laboratories Inc.
E90700, Vol. 1 (936 K)	C-UL	Underwriters Laboratories Inc.
0122085 (677 K)	SEMKO	SEMKO
P01101067 (1638 K)	NEMKO	NEMKO
FI 16812 (964 K)	FIMKO	FIMKO
<u>310684-02</u> (623 K)	DEMKO	DEMKO Testing & Certification
<u>1027742</u> (2305 K)	CSA	Canadian Standards Association

VDE

back to top

Qualification Support

Click on a product for detailed qualification data

Product
<u>H11F3</u>
H11F3300
H11F3300W
H11F33S
H11F33SD
<u>H11F3S</u>
H11F3SD
<u>H11F3W</u>

back to top

© 2007 Fairchild Semiconductor



Products | Design Center | Support | Company News | Investors | My Fairchild | Contact Us | Site Index | Privacy Policy | Site Terms & Conditions | Standard Terms & Conditions (